MJ11021(PNP) MJ11022 (NPN)

Complementary Darlington Silicon Power Transistors

Complementary Darlington Silicon Power Transistors are designed for use as general purpose amplifiers, low frequency switching and motor control applications.

Features

- High dc Current Gain @ 10 Adc h_{FE} = 400 Min (All Types)
- Collector–Emitter Sustaining Voltage
 V_{CEO(sus)} = 250 Vdc (Min) MJ11022, 21
- Low Collector-Emitter Saturation

$$V_{CE(sat)}$$
 = 1.0 V (Typ) @ I_C = 5.0 A
= 1.8 V (Typ) @ I_C = 10 A

• 100% SOA Tested @ $V_{CE} = 44 V$ $I_C = 4.0 A$

t = 250 ms

• Pb-Free Packages are Available*

MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

Dating	Cumple al	Value	Unit
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	250	Vdc
Collector-Base Voltage	V _{CBO}	250	Vdc
Emitter-Base Voltage	V _{EBO}	50	Vdc
Collector Current – Continuous – Peak (Note 1)	Ι _C	15 30	Adc
Base Current	Ι _Β	0.5	Adc
Total Power Dissipation @ T _C = 25°C Derate Above 25°C	P _D	175 1.16	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	−65 to +175 −65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.86	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

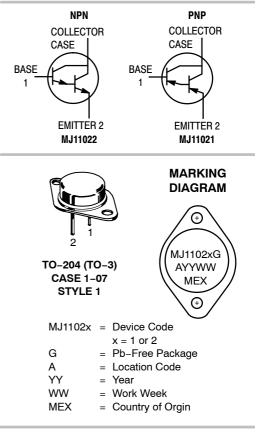
1. Pulse Test: Pulse Width = 5 ms, Duty Cycle \leq 10%.



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15 AMPERE COMPLEMENTARY DARLINGTON POWER TRANSISTORS 250 VOLTS, 175 WATTS



ORDERING INFORMATION

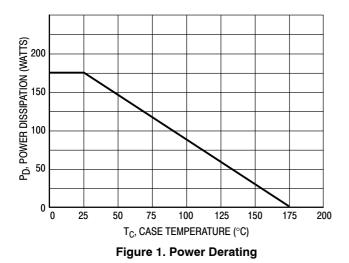
Device	Package	Shipping
MJ11021	TO-3	100 Units/Tray
MJ11021G	TO-3 (Pb-Free)	100 Units/Tray
MJ11022	TO-3	100 Units/Tray
MJ11022G	TO-3 (Pb-Free)	100 Units/Tray

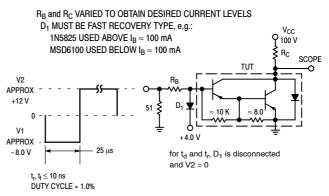
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MJ11021(PNP)

MJ11022 (NPN)





For NPN test circuit reverse diode and voltage polarities.

Figure 2. Switching Times Test Circuit

75

_

h_{fe}

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 1) $(I_C = 0.1 \text{ Adc}, I_B = 0)$	MJ11021, MJ11022	V _{CEO(sus)}	250	_	Vdc
Collector Cutoff Current $(V_{CE} = 125, I_B = 0)$	MJ11021, MJ11022	I _{CEO}	_	1.0	mAdc
$ Collector Cutoff Current \\ (V_{CE} = Rated V_{CB}, V_{BE(off)} = 1.5 Vdc) \\ (V_{CE} = Rated V_{CB}, V_{BE(off)} = 1.5 Vdc, T_J = 150^{\circ}C) $		I _{CEV}		0.5 5.0	mAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)		I _{EBO}	-	2.0	mAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain (I _C = 10 Adc, V_{CE} = 5.0 Vdc) (I _C = 15 Adc, V_{CE} = 5.0 Vdc)		h _{FE}	400 100	15,000 -	_
Collector–Emitter Saturation Voltage ($I_C = 10 \text{ Adc}, I_B = 100 \text{ mA}$) ($I_C = 15 \text{ Adc}, I_B = 150 \text{ mA}$)		V _{CE(sat)}		2.0 3.4	Vdc
Base–Emitter On Voltage $I_{C} = 10 A, V_{CE} = 5.0 Vdc)$		V _{BE(on)}	-	2.8	Vdc
Base-Emitter Saturation Voltage ($I_C = 15$ Adc, $I_B = 150$ mA)		V _{BE(sat)}	-	3.8	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain Bandwidth Product ($I_C = 10 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}, f = 1.0 \text{ MHz}$)		[h _{fe}]	3.0	-	Mhz
Output Capacitance (V _{CB} = 10 Vdc, I_E = 0, f = 0.1 MHz)	MJ11022 MJ11021	C _{ob}		400 600	pF

SWITCHING CHARACTERISTICS

(I_C = 10 Ådc, V_{CE} = 3.0 Vdc, f = 1.0 kHz)

Small-Signal Current Gain

			Typical		
Characteristic		Symbol	NPN	PNP	Unit
Delay Time		t _d	150	75	ns
Rise Time	(V _{CC} = 100 V, I _C = 10 A, I _B = 100 mA	t _r	1.2	0.5	μs
Storage Time	$V_{BE(off)} = 50 \text{ V}$ (See Figure 2)	t _s	4.4	2.7	μs
Fall Time		t _f	10.0	2.5	μs

1. Pulsed Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%.

MJ11021(PNP) MJ11022 (NPN)

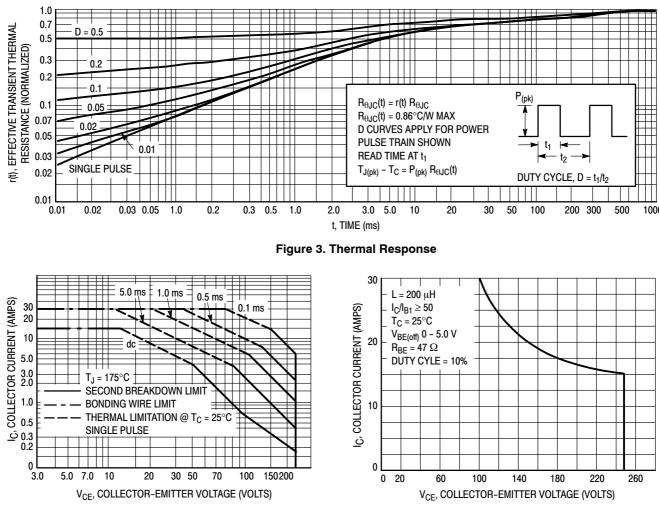


Figure 4. Maximum Rated Forward Bias Safe Operating Area (FBSOA)

FORWARD BIAS

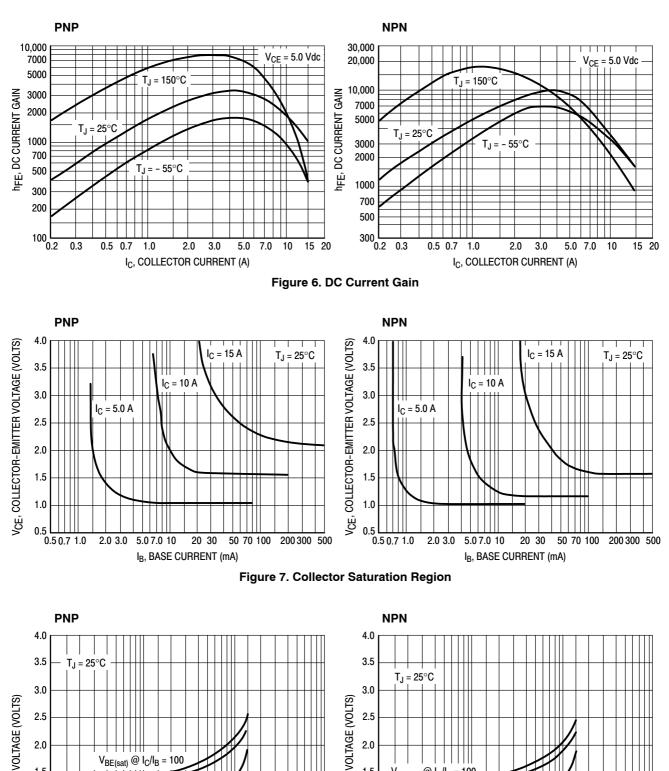
There are two limitations on the power handling ability of a transistor average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 4 is based on $T_{J(pk)} = 175 \,^{\circ}$ C, T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 175 \,^{\circ}$ C. $T_{J(pk)}$ may be calculated from the data in Figure 3. At high case temperatures thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

Figure 5. Maximum RBSOA, Reverse Bias Safe Operating Area

REVERSE BIAS

For inductive loads, high voltage and high current must be sustained simultaneously during turn-off, in most cases, with the base to emitter junction reverse biased. Under these conditions the collector voltage must be hold to a safe level at or below a specific value of collector current. This can be accomplished by several means such as active clamping, RC snubbing, load line shaping, etc. The safe level for these devices is specified as Reverse Bias Safe Operating Area and represents the voltage-current conditions during reverse biased turn-off. This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode. Figure 5 gives ROSOA characteristics.



2.0

1.5

1.0

0.5 L 0.1

70

Figure 8. "On" Voltages

V_{BE(sat)} @ I_C/I_B = 100

V_{BE} @ V_{CE} = 5.0 V

0.2 0.3 0.5 0.7 1.0

V_{CE(sat)} @ I_C/I_B = 100

20 30 50

2.0 3.0 5.0 7.0 10

COLLECTOR CURRENT (AMPS)



2.0 3.0 5.0 7.0 10

COLLECTOR CURRENT (AMPS)

V_{CE(sat)} @ I_C/I_B = 100

20 30 50

V_{BE(sat)} @ I_C/I_B = 100

0.2 0.3 0.5 0.7 1.0

V_{BE} @ V_{CE} = 5.0 V

2.0

1.5

1.0

0.5 0.1

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



DIMENSIONS				
SCALE 1:1	TC	0–204 (TO–3) CASE 1–07 ISSUE Z		DATE 05/18/1988
$ \begin{array}{c} $	$\begin{array}{c} \downarrow \\ C \\ \downarrow \\ -T- \\ PLANE \\ \hline \\ \hline \hline \\ PLANE \\ \hline \\ \hline \\ PLANE \\ \hline \\ \hline \hline \\ \hline \\ PLANE \\ \hline \\ \hline \hline \\ \hline \\ PLANE \\ \hline \\ \hline \hline \hline \\ \hline \hline \hline \\ \hline \hline \hline \\ \hline \hline \hline$	Y 🛞	Y1. 2. CO 3. ALI RE 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	
STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR	STYLE 2: PIN 1. BASE 2. COLLECTOR CASE: EMITTER	STYLE 3: PIN 1. GATE 2. SOURCE CASE: DRAIN	Style 4: Pin 1. ground 2. input Case: output	STYLE 5: PIN 1. CATHODE 2. EXTERNAL TRIP/DELAY CASE: ANODE
STYLE 6: PIN 1. GATE 2. EMITTER CASE: COLLECTOR	STYLE 7: PIN 1. ANODE 2. OPEN CASE: CATHODE	STYLE 8: PIN 1. CATHODE #1 2. CATHODE #2 CASE: ANODE	STYLE 9: PIN 1. ANODE #1 2. ANODE #2 CASE: CATHODE	

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